MOS FET

FL6L52030L

# **Panasonic**

## FL6L52030L

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

#### ■ Features

- Low drain-source ON resistance : RDS (on) typ. = 300 m $\Omega$  ( VGS = -4.0 V )
- Low drive voltage: 2.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

#### ■ Marking Symbol Y3

Established: 2011-03-22

: 2013-10-18

Revised

#### ■ Packaging

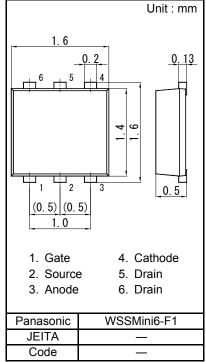
Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

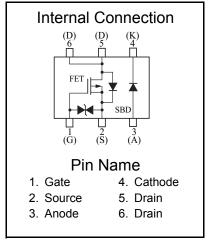
■ Absolute Maximum Ratings Ta = 25 °C

|         |                               | Symbol | Rating      | Unit |
|---------|-------------------------------|--------|-------------|------|
| FET     | Drain to Source Voltage       | VDS    | -20         | V    |
|         | Gate to Source Voltage        | VGS    | ±12         | V    |
|         | Drain current                 | ID     | -1.0        | Α    |
|         | Peak drain current            | IDp    | -4.0        | Α    |
|         | Channel temperature           | Tch    | 150         | °C   |
| SBD     | Reverse voltage               | VR     | 20          | V    |
|         | Forward current (Average)     | IF(AV) | 800         | mA   |
|         | Junction temperature          | Tj     | 125         | °C   |
| Overall | Total power dissipation *1    | PD     | 540         | mW   |
|         | Operating ambient temperature | Topr   | -40 to +85  | °C   |
|         | Storage temperature           | Tstg   | -55 to +125 | °C   |

Note: \*1 Glass epoxy board (25.4 x 25.4 x t0.8 mm) coated with copper foil, which has more than 300mm<sup>2</sup>.

PD absolute maximum rating without a heat shink: 150 mW





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### ■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

| Parameter  | Symbol   | Conditions                          | Min   | Тур  | Max  | Unit   |
|--|----------|-------------------------------------|-------|------|------|--------|
| Drain-source surrender voltage                   | VDSS     | ID = -1.0 mA, VGS = 0               | -20   |      |      | V      |
| Drain-source cutoff current                      | IDSS     | VDS = -20 V, VGS = 0                |       |      | -1.0 | μA     |
| Gate-source cutoff current                       | IGSS     | VGS = ±10 V, VDS = 0                |       |      | ±10  | μA     |
| Gate threshold voltage                           | VTH      | ID = -1.0 mA, VDS = -10 V           | -0.45 | -1.0 | -1.5 | V      |
| Drain-source ON resistance *1                    | RDS(on)  | ID = -0.5 A, VGS = -4.0 V           |       | 300  | 420  | mΩ     |
| Drain-source On resistance                       | KD3(0II) | ID = -0.5 A, VGS = -2.5 V           |       | 420  | 560  | 1112.2 |
| Forward transfer admittance *1                   | Yfs      | ID = -0.5 A, VDS = -10 V, f = 1 kHz | 1.0   |      |      | S      |
| Short-circuit input capacitance (Common source)  | Ciss     |                                     |       | 80   |      |        |
| Short-circuit output capacitance (Common source) | Coss     | VDS = -10 V, VGS = 0 V, f = 1 MHz   |       | 12   |      | pF     |
| Reverse transfer capacitance (Common source)     | Crss     |                                     |       | 12   |      |        |
| Turn-on delay time *2                            | td(on)   | VDD = -15 V, VGS = 0 to - 4.0 V     |       | 12   |      | no     |
| Rise time *2                                     | tr       | ID = -0.5 A                         |       | 6    |      | ns     |
| Turn-off delay time *2                           | td(off)  | VDD = -15 V, VGS = - 4.0 to 0 V     |       | 17   |      | ne     |
| Fall time *2                                     | tf       | ID = -0.5 A                         |       | 10   |      | ns     |

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

#### **SBD**

| Parameter       | Symbol | Conditions  | Min | Тур | Max  | Unit |
|-----------------|--------|-------------|-----|-----|------|------|
| Forward voltage | VF     | IF = 800 mA |     |     | 0.47 | V    |
| Reverse current | IR     | VR = 20 V   |     |     | 80   | μA   |

Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring Note: methods for diodes.

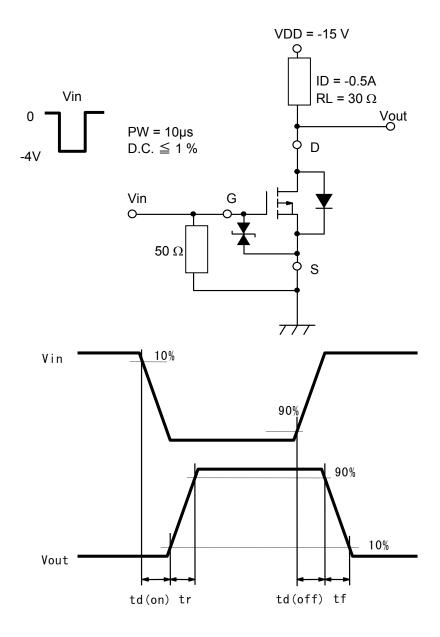
<sup>2. \*1</sup> Pulse measurement

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



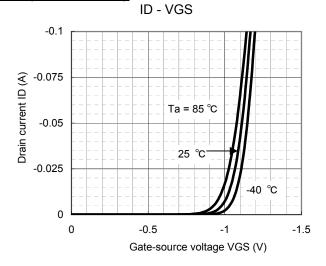
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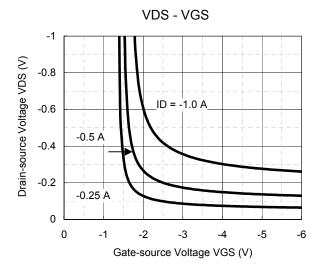
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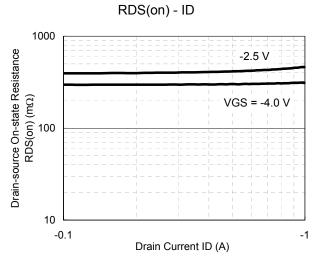
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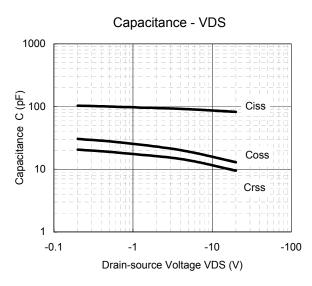
# Technical Data (reference)

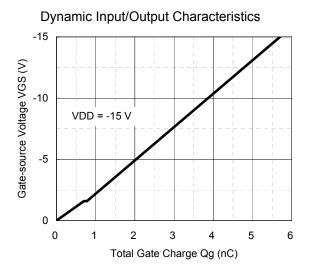
ID - VDS -1 -0.9 -0.8 Drain current ID (A) -0.7 -0.6 -0.5 -1.5 V -0.4 -0.3 -0.2 -1.0 V -0.1 0 0 -0.2 -0.3 -0.4 -0.5 -0.6 -0.1 Drain-source voltage VDS (V)









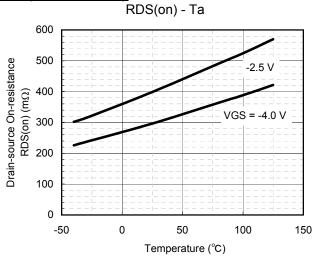


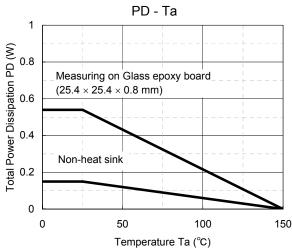
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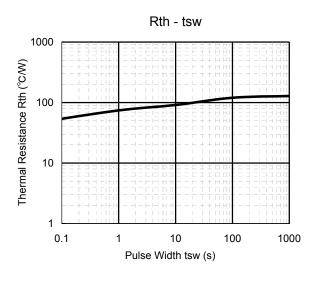
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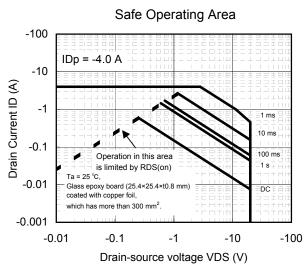
## Technical Data (reference)

-1.5 Output Source Threshold Voltage -0.5 Output Source -0.5 Output So









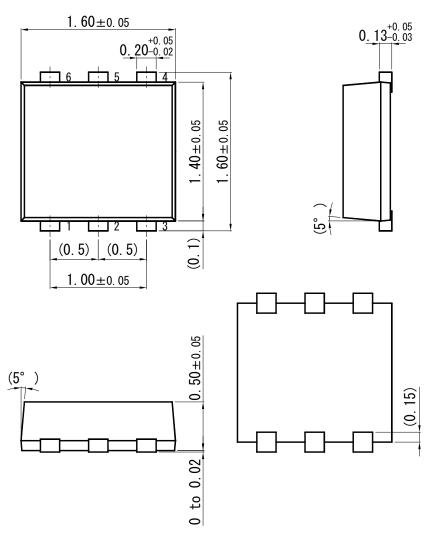
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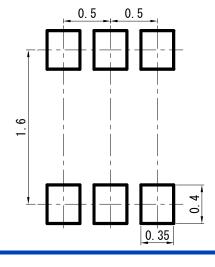
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WSSMini6-F1

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm)



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